

Ivan G Ivanov

List of Publications by Citations

Source: <https://exaly.com/author-pdf/7659917/ivan-g-ivanov-publications-by-citations.pdf>

Version: 2024-04-19

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

205
papers

3,380
citations

31
h-index

48
g-index

214
ext. papers

3,800
ext. citations

3.1
avg, IF

4.98
L-index

#	Paper	IF	Citations
205	Vibrational properties and structure of undoped and Al-doped ZnO films deposited by RF magnetron sputtering. <i>Thin Solid Films</i> , 2000 , 379, 28-36	2.2	209
204	Annealing effects on optical properties of low temperature grown ZnO nanorod arrays. <i>Journal of Applied Physics</i> , 2009 , 105, 053503	2.5	116
203	Growth of SiC by Hot-Wall CVD and HTCVD. <i>Physica Status Solidi (B): Basic Research</i> , 1997 , 202, 321-334	1.3	115
202	High temperature chemical vapor deposition of SiC. <i>Applied Physics Letters</i> , 1996 , 69, 1456-1458	3.4	101
201	High-fidelity spin and optical control of single silicon-vacancy centres in silicon carbide. <i>Nature Communications</i> , 2019 , 10, 1954	17.4	99
200	Properties of molecular-beam epitaxy-grown GaNAs from optical spectroscopy. <i>Journal of Applied Physics</i> , 1998 , 84, 3830-3835	2.5	80
199	Nitrogen doping concentration as determined by photoluminescence in 4H and 6H SiC. <i>Journal of Applied Physics</i> , 1996 , 80, 3504-3508	2.5	80
198	Properties of the D1 bound exciton in 4H SiC. <i>Physical Review B</i> , 1999 , 59, 1956-1963	3.3	72
197	Correlation between the antisite pair and the DI center in SiC. <i>Physical Review B</i> , 2003 , 67,	3.3	66
196	Quantum Properties of Dichroic Silicon Vacancies in Silicon Carbide. <i>Physical Review Applied</i> , 2018 , 9,	4.3	65
195	Liquid phase epitaxial growth of SiC. <i>Journal of Crystal Growth</i> , 1999 , 197, 147-154	1.6	62
194	The influence of the substrate material on the growth of V2O5 flash-evaporated films. <i>Applied Surface Science</i> , 1995 , 90, 389-391	6.7	60
193	Extremely high quantum efficiency of donor-acceptor-pair emission in N-and-B-doped 6H-SiC. <i>Journal of Applied Physics</i> , 2006 , 99, 093108	2.5	59
192	Photoluminescence of electron-irradiated 4H SiC. <i>Physical Review B</i> , 1999 , 59, 8008-8014	3.3	57
191	Growth of thick GaN layers with hydride vapour phase epitaxy. <i>Journal of Crystal Growth</i> , 2005 , 281, 17-316	3.6	51
190	Layer-number determination in graphene on SiC by reflectance mapping. <i>Carbon</i> , 2014 , 77, 492-500	10.4	46
189	Developing silicon carbide for quantum spintronics. <i>Applied Physics Letters</i> , 2020 , 116, 190501	3.4	45

188	Stable and metastable Si negative-U centers in AlGa _N and AlN. <i>Applied Physics Letters</i> , 2014 , 105, 162106	3.4	41
187	Ionization energies of phosphorus and nitrogen donors and aluminum acceptors in 4H silicon carbide from the donor-acceptor pair emission. <i>Physical Review B</i> , 2005 , 71,	3.3	40
186	Raman and IR study of cobalt acetate dihydrate. <i>Journal of Molecular Structure</i> , 1995 , 354, 119-125	3.4	38
185	Lateral Enlargement Growth Mechanism of 3C-SiC on Off-Oriented 4H-SiC Substrates. <i>Crystal Growth and Design</i> , 2014 , 14, 6514-6520	3.5	37
184	Electrical Charge State Manipulation of Single Silicon Vacancies in a Silicon Carbide Quantum Optoelectronic Device. <i>Nano Letters</i> , 2019 , 19, 7173-7180	11.5	36
183	Identification and tunable optical coherent control of transition-metal spins in silicon carbide. <i>Npj Quantum Information</i> , 2018 , 4,	8.6	35
182	CFx thin solid films deposited by high power impulse magnetron sputtering: Synthesis and characterization. <i>Surface and Coatings Technology</i> , 2011 , 206, 646-653	4.4	34
181	Fast growth of high quality GaN. <i>Physica Status Solidi A</i> , 2003 , 200, 13-17		34
180	High-Quality 2" Bulk-Like Free-Standing GaN Grown by Hydride Vapour Phase Epitaxy on a Si-doped Metal Organic Vapour Phase Epitaxial GaN Template with an Ultra Low Dislocation Density. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 1181-1185	1.4	34
179	Excitation properties of the divacancy in 4H-SiC. <i>Physical Review B</i> , 2018 , 98,	3.3	33
178	Vibrational modifications on lithium intercalation in V ₂ O ₅ films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1995 , 33, 168-172	3.1	32
177	Single Domain 3C-SiC Growth on Off-Oriented 4H-SiC Substrates. <i>Crystal Growth and Design</i> , 2015 , 15, 2940-2947	3.5	31
176	Defects in N, O and N, Zn implanted ZnO bulk crystals. <i>Journal of Applied Physics</i> , 2013 , 113, 103509	2.5	31
175	Contribution of free-electron recombination to the luminescence spectra of thick GaN films grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 1999 , 85, 7888-7892	2.5	31
174	Direct observation of large-scale nonuniformities in hydride vapor-phase epitaxy-grown gallium nitride by cathodoluminescence. <i>Applied Physics Letters</i> , 1998 , 73, 3583-3585	3.4	30
173	Tunable laser spectroscopy of spin injection in ZnMnSe/ZnCdSe quantum structures. <i>Applied Physics Letters</i> , 2002 , 81, 2196-2198	3.4	29
172	The material quality of CVD-grown SiC using different carbon precursors. <i>Journal of Crystal Growth</i> , 1998 , 183, 163-174	1.6	28
171	Vibrational studies of copper thiogallate solid solutions. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 57, 102-109	3.1	28

170	Nanoscale phenomena ruling deposition and intercalation of AlN at the graphene/SiC interface. <i>Nanoscale</i> , 2020 , 12, 19470-19476	7.7	28
169	Real-time sensing of lead with epitaxial graphene-integrated microfluidic devices. <i>Sensors and Actuators B: Chemical</i> , 2019 , 288, 425-431	8.5	26
168	Phonon replicas at the M point in 4H-SiC: A theoretical and experimental study. <i>Physical Review B</i> , 1998 , 58, 13634-13647	3.3	26
167	Considerably long carrier lifetimes in high-quality 3C-SiC(111). <i>Applied Physics Letters</i> , 2012 , 100, 252101	3.4	25
166	In-grown stacking faults in 4H-SiC epilayers grown on off-cut substrates. <i>Journal of Applied Physics</i> , 2009 , 105, 123513	2.5	25
165	Analysis of the sharp donor-acceptor pair luminescence in 4H-SiC doped with nitrogen and aluminum. <i>Physical Review B</i> , 2003 , 67,	3.3	25
164	High-resolution x-ray analysis of InGaN/GaN superlattices grown on sapphire substrates with GaN layers. <i>Applied Physics Letters</i> , 1996 , 69, 3390-3392	3.4	25
163	Uniform hot-wall MOCVD epitaxial growth of 2 inch AlGaN/GaN HEMT structures. <i>Journal of Crystal Growth</i> , 2007 , 300, 100-103	1.6	24
162	The growth of V2O5 flash-evaporated films. <i>Journal of Materials Science Letters</i> , 1995 , 14, 934-936		24
161	Characterization of the ternary compounds AgGaTe ₂ and AgGa ₅ Te ₈ . <i>Journal of Materials Science</i> , 1996 , 31, 3315-3319	4.3	24
160	Graphene self-switching diodes as zero-bias microwave detectors. <i>Applied Physics Letters</i> , 2015 , 106, 093116	3.4	23
159	Reduction of structural defects in thick 4H-SiC epitaxial layers grown on 4° off-axis substrates. <i>Journal of Applied Physics</i> , 2013 , 113, 223502	2.5	23
158	Raman study of complexation in aqueous solutions of magnesium acetate. <i>Journal of Molecular Structure</i> , 1996 , 377, 13-17	3.4	23
157	Ga-bound excitons in 3C-, 4H-, and 6H-SiC. <i>Physical Review B</i> , 1996 , 53, 13503-13506	3.3	22
156	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. <i>Carbon</i> , 2017 , 116, 722-732	10.4	21
155	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties of Ga _x P _{1-x} alloys: A proof for a general property of dilute nitrides. <i>Physical Review B</i> , 2004 , 70,	3.3	21
154	Hydride vapor-phase epitaxial GaN thick films for quasi-substrate applications: Strain distribution and wafer bending. <i>Journal of Electronic Materials</i> , 2004 , 33, 389-394	1.9	20
153	Surface functionalization of epitaxial graphene on SiC by ion irradiation for gas sensing application. <i>Applied Surface Science</i> , 2017 , 403, 707-716	6.7	19

152	Performance tuning of gas sensors based on epitaxial graphene on silicon carbide. <i>Materials and Design</i> , 2018 , 153, 153-158	8.1	19
151	Atomic layer deposition of InN using trimethylindium and ammonia plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2019 , 37, 020926	2.9	18
150	A comparative study of direct current magnetron sputtering and high power impulse magnetron sputtering processes for CN _x thin film growth with different inert gases. <i>Diamond and Related Materials</i> , 2016 , 64, 13-26	3.5	18
149	Recombination centers in as-grown and electron-irradiated ZnO substrates. <i>Journal of Applied Physics</i> , 2007 , 102, 093504	2.5	17
148	Defects in SiC. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 15-24	2.8	17
147	The growth and electrochemical properties of V6O13 flash-evaporated films. <i>Solid State Ionics</i> , 1995 , 76, 133-141	3.3	17
146	Rolling performance of carbon nitride-coated bearing components in different lubrication regimes. <i>Tribology International</i> , 2017 , 114, 141-151	4.9	16
145	Monitoring of epitaxial graphene anodization. <i>Electrochimica Acta</i> , 2017 , 238, 91-98	6.7	16
144	Probing the uniformity of hydrogen intercalation in quasi-free-standing epitaxial graphene on SiC by micro-Raman mapping and conductive atomic force microscopy. <i>Nanotechnology</i> , 2019 , 30, 284003	3.4	16
143	Raman probing of hydrogen-intercalated graphene on Si-face 4H-SiC. <i>Materials Science in Semiconductor Processing</i> , 2019 , 96, 145-152	4.3	16
142	Quasi-free-standing monolayer and bilayer graphene growth on homoepitaxial on-axis 4H-SiC(0 0 0 1) layers. <i>Carbon</i> , 2015 , 82, 12-23	10.4	16
141	In-situ terahertz optical Hall effect measurements of ambient effects on free charge carrier properties of epitaxial graphene. <i>Scientific Reports</i> , 2017 , 7, 5151	4.9	16
140	CVD Growth and Characterisation of SiC Epitaxial Layers on Faces Perpendicular to the (0001) Basal Plane. <i>Materials Science Forum</i> , 1998 , 264-268, 123-126	0.4	16
139	Seed-Layer-Free Atomic Layer Deposition of Highly Uniform Al ₂ O ₃ Thin Films onto Monolayer Epitaxial Graphene on Silicon Carbide. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1900097	4.6	15
138	In Situ Activation of an Indium(III) Triazenide Precursor for Epitaxial Growth of Indium Nitride by Atomic Layer Deposition. <i>Chemistry of Materials</i> , 2020 , 32, 4481-4489	9.6	15
137	Large-area free-standing GaN substrate grown by hydride vapor phase epitaxy on epitaxial lateral overgrown GaN template. <i>Physica B: Condensed Matter</i> , 2006 , 371, 133-139	2.8	15
136	Homoepitaxial On-Axis Growth of 4H- and 6H-SiC by CVD. <i>Materials Science Forum</i> , 2004 , 457-460, 193-196	0.4	15
135	Optical selection rules for shallow donors in 4H-SiC and ionization energy of the nitrogen donor at the hexagonal site. <i>Physical Review B</i> , 2003 , 67,	3.3	15

134	Reactive high power impulse magnetron sputtering of CF _x thin films in mixed Ar/CF ₄ and Ar/C ₄ F ₈ discharges. <i>Thin Solid Films</i> , 2013 , 542, 21-30	2.2	14
133	Process stability and morphology optimization of very thick 4H-SiC epitaxial layers grown by chloride-based CVD. <i>Journal of Crystal Growth</i> , 2013 , 380, 55-60	1.6	14
132	High Growth Rate of SiC by Sublimation Epitaxy. <i>Materials Science Forum</i> , 1998 , 264-268, 143-146	0.4	14
131	Optical and Electrical Properties of Ga ₂ Te ₃ Crystals. <i>Physica Status Solidi A</i> , 1994 , 145, 207-215		14
130	Lead (Pb) interfacing with epitaxial graphene. <i>Physical Chemistry Chemical Physics</i> , 2018 , 20, 17105-17116	6.6	14
129	The Endocyclic Carbon Substituent of Guanidinate and Amidinate Precursors Controlling Atomic Layer Deposition of InN Films. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 25691-25700	3.8	13
128	Exciton dynamics in homoepitaxial GaN. <i>Solid State Communications</i> , 1997 , 104, 205-209	1.6	13
127	Elimination of step bunching in the growth of large-area monolayer and multilayer graphene on off-axis 3C SiC (111). <i>Carbon</i> , 2018 , 140, 533-542	10.4	12
126	On the use of methane as a carbon precursor in Chemical Vapor Deposition of silicon carbide. <i>Journal of Crystal Growth</i> , 2014 , 390, 24-29	1.6	12
125	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1462-1466	2.8	12
124	Magnetic resonance identification of hydrogen at a zinc vacancy in ZnO. <i>Journal of Physics Condensed Matter</i> , 2013 , 25, 335804	1.8	12
123	A SIMS study on Mg diffusion in Zn _{0.94} Mg _{0.06} O/ZnO heterostructures grown by metal organic chemical vapor deposition. <i>Applied Surface Science</i> , 2011 , 257, 8629-8633	6.7	12
122	Growth and Characterisation of Thick SiC Epilayers by High Temperature CVD. <i>Materials Science Forum</i> , 1998 , 264-268, 103-106	0.4	12
121	Energy levels and charge state control of the carbon antisite-vacancy defect in 4H-SiC. <i>Applied Physics Letters</i> , 2019 , 114, 212105	3.4	11
120	Low-temperature growth of low friction wear-resistant amorphous carbon nitride thin films by mid-frequency, high power impulse, and direct current magnetron sputtering. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 05E112	2.9	11
119	Experimental study of the effect of local atomic ordering on the energy band gap of melt grown InGaAsN alloys. <i>Semiconductor Science and Technology</i> , 2017 , 32, 085005	1.8	10
118	Effect of epitaxial graphene morphology on adsorption of ambient species. <i>Applied Surface Science</i> , 2019 , 486, 239-248	6.7	10
117	Optical and morphological features of bulk and homoepitaxial ZnO. <i>Superlattices and Microstructures</i> , 2006 , 39, 247-256	2.8	10

116	Temperature-Dependent Hall Effect Measurements in Low Γ -Compensated p-Type 4H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 677-680	0.4	10
115	Resonant sharp hot free-exciton luminescence in 6H- and 4H-SiC due to inhibited exciton-phonon interaction. <i>Physical Review B</i> , 2001 , 64,	3.3	10
114	Ligand hyperfine interactions at silicon vacancies in 4H-SiC. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 195501	1.8	9
113	Silicon carbonitride thin films deposited by reactive high power impulse magnetron sputtering. <i>Surface and Coatings Technology</i> , 2018 , 335, 248-256	4.4	9
112	Trimethylboron as Single-Source Precursor for Boron Γ Carbon Thin Film Synthesis by Plasma Chemical Vapor Deposition. <i>Journal of Physical Chemistry C</i> , 2016 , 120, 21990-21997	3.8	9
111	High-Resolution Raman and Luminescence Spectroscopy of Isotope-Pure $^{28}\text{Si}^{12}\text{C}$, Natural and ^{13}C Γ -Enriched 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 471-474	0.4	9
110	EPR and ENDOR Studies of Shallow Donors in SiC. <i>Applied Magnetic Resonance</i> , 2010 , 39, 49-85	0.8	9
109	Understanding Graphene Response to Neutral and Charged Lead Species: Theory and Experiment. <i>Materials</i> , 2018 , 11,	3.5	9
108	Surface photovoltage and photoluminescence study of thick Ga(In)AsN layers grown by liquid-phase epitaxy. <i>Journal of Physics: Conference Series</i> , 2016 , 700, 012028	0.3	8
107	Modified Epitaxial Graphene on SiC for Extremely Sensitive and Selective Gas Sensors. <i>Materials Science Forum</i> , 2016 , 858, 1145-1148	0.4	8
106	Negative-U behavior of the Si donor in Al $_{0.77}$ Ga $_{0.23}$ N. <i>Applied Physics Letters</i> , 2013 , 103, 042101	3.4	8
105	Control of Epitaxial Graphene Thickness on 4H-SiC(0001) and Buffer Layer Removal through Hydrogen Intercalation. <i>Materials Science Forum</i> , 2012 , 717-720, 605-608	0.4	8
104	Micro-Raman scattering profiling studies on HVPE-grown free-standing GaN. <i>Physica Status Solidi A</i> , 2004 , 201, 2773-2776		8
103	Highly homogeneous bulk-like Γ -GaN grown by HVPE on MOCVD Γ -GaN template. <i>Journal of Crystal Growth</i> , 2005 , 275, e387-e393	1.6	8
102	Thick GaN Layers Grown on A-plane Sapphire Substrates by Hydride Vapour Phase Epitaxy. <i>Physica Scripta</i> , 1999 , T79, 67	2.6	8
101	Surface functionalization of epitaxial graphene using ion implantation for sensing and optical applications. <i>Carbon</i> , 2020 , 157, 169-184	10.4	8
100	Surface engineering of SiC via sublimation etching. <i>Applied Surface Science</i> , 2016 , 390, 816-822	6.7	8
99	A comparative study of high-quality C-face and Si-face 3C-SiC(1 1 1) grown on off-oriented 4H-SiC substrates. <i>Journal Physics D: Applied Physics</i> , 2019 , 52, 345103	3	7

98	Calibration on wide-ranging aluminum doping concentrations by photoluminescence in high-quality uncompensated p-type 4H-SiC. <i>Applied Physics Letters</i> , 2017 , 111, 072101	3.4	7
97	Brominated Chemistry for Chemical Vapor Deposition of Electronic Grade SiC. <i>Chemistry of Materials</i> , 2015 , 27, 793-801	9.6	7
96	Effective-mass approximation for shallow donors in uniaxial indirect band-gap crystals and application to 4H-SiC. <i>Physical Review B</i> , 2006 , 73,	3.3	7
95	Anti-site pair in SiC: a model of the DI center. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 175-179	2.8	7
94	SiC and III-Nitride Growth in Hot-Wall CVD Reactor. <i>Materials Science Forum</i> , 2005 , 483-485, 61-66	0.4	7
93	Excitation properties of hydrogen-related photoluminescence in 6H-SiC. <i>Physical Review B</i> , 2000 , 62, 7162-7168	3.3	7
92	Metastability of a Hydrogen-related Defect in 6H-SiC. <i>Materials Science Forum</i> , 2000 , 338-342, 651-654	0.4	7
91	Exciton Dynamics in Homoepitaxial GaN. <i>Materials Science Forum</i> , 1998 , 264-268, 1275-1278	0.4	7
90	Phonons in polymorphous PbTe films. II. Infrared and Raman spectra of PbTe and PbTe:Cr films on KCl substrates. <i>Journal of Physics Condensed Matter</i> , 1992 , 4, 4645-4652	1.8	7
89	Layer quality of Sb-doped GaAs grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 1993 , 129, 143-148	1.6	7
88	Spin-relaxation times exceeding seconds for color centers with strong spin-orbit coupling in SiC. <i>New Journal of Physics</i> , 2020 , 22, 103051	2.9	7
87	Reactive sputtering of CS _x thin solid films using CS ₂ as precursor. <i>Vacuum</i> , 2020 , 182, 109775	3.7	6
86	Light emission enhancement from ZnO nanostructured films grown on Gr/SiC substrates. <i>Carbon</i> , 2016 , 99, 295-301	10.4	6
85	Assessment of H-intercalated graphene for microwave FETs through material characterization and electron transport studies. <i>Carbon</i> , 2015 , 81, 96-104	10.4	6
84	High quality 4H-SiC grown on various substrate orientations. <i>Diamond and Related Materials</i> , 1997 , 6, 1289-1292	3.5	6
83	Cathodoluminescence of Defect Regions in SiC Epi-Films. <i>Materials Science Forum</i> , 1998 , 264-268, 653-656	4	6
82	Zeeman spectroscopy of the D1 bound exciton in 3C- and 4H-SiC. <i>Physica B: Condensed Matter</i> , 1999 , 273-274, 677-680	2.8	6
81	Interplay between thin silver films and epitaxial graphene. <i>Surface and Coatings Technology</i> , 2020 , 381, 125200	4.4	6

80	CVD growth and properties of on-axis vanadium doped semi-insulating 4H-SiC epilayers. <i>Journal of Applied Physics</i> , 2019 , 125, 045702	2.5	6
79	Probing the uniformity of silver-doped epitaxial graphene by micro-Raman mapping. <i>Physica B: Condensed Matter</i> , 2020 , 580, 411751	2.8	6
78	MOCVD of AlN on epitaxial graphene at extreme temperatures. <i>CrystEngComm</i> , 2021 , 23, 385-390	3.3	6
77	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. <i>Physical Review B</i> , 2015 , 92,	3.3	5
76	Ionization energy of the phosphorus donor in 3C-SiC from the donor-acceptor pair emission. <i>Journal of Applied Physics</i> , 2010 , 108, 063532	2.5	5
75	Effective-Mass Theory of Shallow Donors in 4H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 511-514	0.4	5
74	Characterization of crack-free relaxed GaN grown on 2 \times 2 sapphire. <i>Journal of Applied Physics</i> , 2005 , 98, 073525	2.5	5
73	Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells. <i>Thin Solid Films</i> , 2000 , 364, 224-227	2.2	5
72	High-temperature excitons in GaAs quantum wells embedded in AlAs/GaAs superlattices. <i>Vacuum</i> , 2000 , 58, 478-484	3.7	5
71	B implantation in 6H-SiC: Lattice damage recovery and implant activation upon high-temperature annealing. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1040		5
70	Photoluminescence of 4H-SiC: some remarks. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 234-238	3.1	5
69	Direct epitaxial nanometer-thin InN of high structural quality on 4H-SiC by atomic layer deposition. <i>Applied Physics Letters</i> , 2020 , 117, 093101	3.4	5
68	Excitonic emission in heavily Ga-doped zinc oxide films grown on GaN. <i>Journal of Luminescence</i> , 2020 , 223, 117265	3.8	4
67	Optical properties of thick GaInAs(Sb)N layers grown by liquid-phase epitaxy. <i>Journal of Physics: Conference Series</i> , 2017 , 794, 012013	0.3	4
66	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study 2014 ,		4
65	Growth of 4H-SiC from liquid phase. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 46, 329-332	3.1	4
64	The D1 Exciton in 4H-SiC. <i>Physica Status Solidi (B): Basic Research</i> , 1998 , 210, 337-340	1.3	4
63	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. <i>Journal of Crystal Growth</i> , 2008 , 310, 1006-1009	1.6	4

62	Influence of dislocation density on photoluminescence intensity of GaN. <i>Journal of Crystal Growth</i> , 2005 , 278, 406-410	1.6	4
61	Excitation spectra of nitrogen bound excitons in 4H- and 6H-SiC. <i>Journal of Applied Physics</i> , 2002 , 91, 2028-2032	2.5	4
60	Photoconductivity of Lightly-Doped and Semi-Insulating 4H-SiC and the Free Exciton Binding Energy. <i>Materials Science Forum</i> , 2002 , 389-393, 613-616	0.4	4
59	Pseudo-Donors in SiC. <i>Materials Science Forum</i> , 2000 , 338-342, 647-650	0.4	4
58	Photoluminescence excitation spectra of the free exciton emission in 6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 265-269	3.1	4
57	Exploring the Interface Landscape of Noble Metals on Epitaxial Graphene. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2000673	1.6	4
56	Charge state control of the silicon vacancy and divacancy in silicon carbide. <i>Journal of Applied Physics</i> , 2021 , 129, 215702	2.5	4
55	Clustering and Morphology Evolution of Gold on Nanostructured Surfaces of Silicon Carbide: Implications for Catalysis and Sensing. <i>ACS Applied Nano Materials</i> , 2021 , 4, 1282-1293	5.6	4
54	Splitting of type-I (N-B, P-Al) and type-II (N-Al, N-Ga) donor-acceptor pair spectra in 3C-SiC. <i>Physical Review B</i> , 2011 , 83,	3.3	3
53	Characterization of High-Quality Free-Standing GaN Grown by HVPE. <i>Physica Scripta</i> , 2004 , T114, 18-21	2.6	3
52	Photoluminescence line-shape analysis in quantum wells embedded in superlattices. <i>Materials Science and Engineering C</i> , 2001 , 15, 75-77	8.3	3
51	Photoluminescence upconversion in 4H-SiC. <i>Applied Physics Letters</i> , 2002 , 81, 2547-2549	3.4	3
50	Some Aspects of the Photoluminescence and Raman Spectroscopy of (10-10)- and (11-20)-Oriented 4H and 6H Silicon Carbide. <i>Materials Science Forum</i> , 1998 , 264-268, 469-472	0.4	3
49	Spectral Behavior of Zero-Bias Photocurrent at Low Temperature in Bulk Semi-Insulating GaAs : Cr. <i>Journal of the Electrochemical Society</i> , 1994 , 141, 2533-2536	3.9	3
48	Growth optimization and applicability of thick on-axis SiC layers using sublimation epitaxy in vacuum. <i>Journal of Crystal Growth</i> , 2016 , 448, 51-57	1.6	3
47	Resolving mobility anisotropy in quasi-free-standing epitaxial graphene by terahertz optical Hall effect. <i>Carbon</i> , 2021 , 172, 248-259	10.4	3
46	Deep levels related to the carbon antisite-vacancy pair in 4H-SiC. <i>Journal of Applied Physics</i> , 2021 , 130, 065703	2.5	3
45	Wafer-scale epitaxial graphene on SiC for sensing applications 2015 ,		2

44	Optical characterization of MBE-grown GaNAs. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 50, 153-156	3.1	2
43	Magnetic resonance studies of defects in electron-irradiated ZnO substrates. <i>Physica B: Condensed Matter</i> , 2007 , 401-402, 507-510	2.8	2
42	Effect of non-abrupt interfaces in AlAs/GaAs superlattices with embedded GaAs quantum wells. <i>Vacuum</i> , 2000 , 58, 561-567	3.7	2
41	Near Band-Gap Emission in V-Implanted and Annealed 4H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 497-500	0.4	2
40	Domain Structure of Thick GaN Layers Grown by Hydride Vapor Phase Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		2
39	Manipulation of epitaxial graphene towards novel properties and applications. <i>Materials Today: Proceedings</i> , 2020 , 20, 37-45	1.4	2
38	Chloride-based SiC growth on a-axis 4H-SiC substrates. <i>Physica B: Condensed Matter</i> , 2016 , 480, 23-25	2.8	1
37	Anodization study of epitaxial graphene: insights on the oxygen evolution reaction of graphitic materials. <i>Nanotechnology</i> , 2019 , 30, 285701	3.4	1
36	Epitaxial Graphene Growth on the Step-Structured Surface of Off-Axis C-Face 3C-SiC(100100). <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900718	1.3	1
35	A patterning-free approach for growth of free-standing graphene nanoribbons using step-bunched facets of off-oriented 4H-SiC(0 0 0 1) epilayers. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 115102	3	1
34	Defects in silicon carbide grown by fluorinated chemical vapor deposition chemistry. <i>Physica B: Condensed Matter</i> , 2018 , 535, 44-49	2.8	1
33	Bioelectrocatalysis on Anodized Epitaxial Graphene and Conventional Graphitic Interfaces. <i>ChemElectroChem</i> , 2019 , 6, 3791-3796	4.3	1
32	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Transactions</i> , 2017 , 80, 107-115		1
31	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 405-408	0.4	1
30	Photoluminescence of 8H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 347-350	0.4	1
29	Investigation of Intrinsic Carbon-Related Defects in 4H-SiC by Selective-Excitation Photoluminescence Spectroscopy. <i>Materials Science Forum</i> , 2012 , 717-720, 259-262	0.4	1
28	Wave-Function Symmetry and the Properties of Shallow P Donors in 4H SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 445-448	0.4	1
27	Antisites as Possible Origin of Irradiation Induced Photoluminescence Centers in SiC: A Theoretical Study on Clusters of Antisites and Carbon Interstitials in 4H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 443-448	0.4	1

26	Donor-Acceptor Pair Luminescence in 4H-SiC Doped with Nitrogen and Aluminum. <i>Materials Science Forum</i> , 2003 , 433-436, 321-324	0.4	1
25	Hot-wall MOCVD grown homoepitaxial GaN layers with intense intrinsic excitonic structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 739-743	1.6	1
24	Bound Exciton Recombination in Electron Irradiated 4H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 477-480	0.4	1
23	Optical Properties of GaNAs Grown by MBE. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1998 , 3, 1		1
22	Raman scattering study of crystal perfection of MOVPE-grown GaAs. <i>Semiconductor Science and Technology</i> , 1993 , 8, 179-184	1.8	1
21	Silver nanoparticle array on weakly interacting epitaxial graphene substrate as catalyst for hydrogen evolution reaction under neutral conditions. <i>Applied Physics Letters</i> , 2021 , 119, 153902	3.4	1
20	First-Principles Study on Photoluminescence Quenching of Divacancy in 4H SiC. <i>Materials Science Forum</i> , 2019 , 963, 714-717	0.4	1
19	Iron Oxide Nanoparticle Decorated Graphene for Ultra-Sensitive Detection of Volatile Organic Compounds. <i>Proceedings (mdpi)</i> , 2018 , 2, 985	0.3	1
18	Bidirectional Hydrogen Electrocatalysis on Epitaxial Graphene.. <i>ACS Omega</i> , 2022 , 7, 13221-13227	3.9	1
17	Theory of the Stark Effect on the Donor Levels in 4H Silicon Carbide. <i>Materials Science Forum</i> , 2007 , 556-557, 435-438	0.4	0
16	Intrinsic Photoconductivity of 6H-SiC and the Free-Exciton Binding Energy. <i>Materials Science Forum</i> , 2001 , 353-356, 405-408	0.4	0
15	Changes in the Exciton-Related Photoluminescence of 4H- and 6H-SiC Induced by Uniaxial Stress. <i>Materials Science Forum</i> , 1998 , 264-268, 489-492	0.4	0
14	Critical View on Buffer Layer Formation and Monolayer Graphene Properties in High-Temperature Sublimation. <i>Applied Sciences (Switzerland)</i> , 2021 , 11, 1891	2.6	0
13	Study of Cucurbit[7]uril nanocoating on epitaxial graphene to design a versatile sensing platform. <i>Applied Surface Science</i> , 2021 , 563, 150096	6.7	0
12	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P741-P745	2	
11	Resonant ionization of shallow donors in electric field. <i>Physica Scripta</i> , 2014 , 89, 085802	2.6	
10	Morphology Optimization of Very Thick 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2013 , 740-742, 251-254	0.4	
9	Temperature Dependence and Selective Excitation of the Phosphorus Related Photoluminescence in 4H-SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 263-266	0.4	

- 8 Donor-Acceptor Pair Luminescence of P-Al and N-Al Pairs in 3C-SiC and the Ionization Energy of the P Donor. *Materials Science Forum*, **2011**, 679-680, 245-248 0.4
- 7 Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. *Materials Science Forum*, **2012**, 717-720, 211-216 0.4
- 6 Donor-Acceptor Pair Luminescence of Phosphorus-Aluminum and Nitrogen-Aluminum Pairs in 4H SiC. *Materials Science Forum*, **2006**, 527-529, 601-604 0.4
- 5 Photoluminescence Excitation Spectroscopy on the Donor-Acceptor Pair Luminescence in 4H and 6H SiC. *Materials Science Forum*, **2004**, 457-460, 585-588 0.4
- 4 Photoluminescence Up-Conversion Processes in SiC. *Materials Science Forum*, **2003**, 433-436, 309-312 0.4
- 3 Spin Polarization and Injection in ZnMnSe/ZnCdSe Heterostructures. *Materials Research Society Symposia Proceedings*, **2001**, 690, F1.7.1
- 2 6H-SiC Crystallinity Behaviour upon B Implantation Studied by Raman Scattering. *Materials Science Forum*, **1998**, 264-268, 741-744 0.4
- 1 Ga Bound Excitons in 6H-SiC. *Materials Science Forum*, **1995**, 196-201, 91-96 0.4